PROCESS CP324

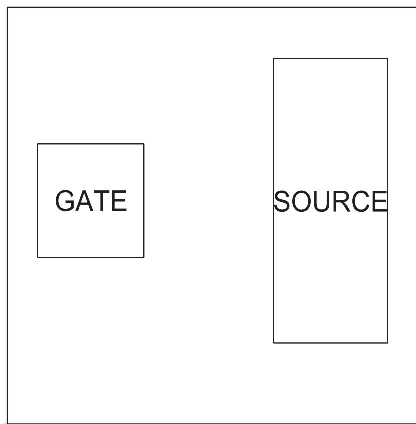
Small Signal MOSFET Transistor

N-Channel Enhancement-Mode Transistor Chip

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	21.65 x 21.65 MILS
Die Thickness	9.0 MILS
Gate Bonding Pad Area	5.5 x 5.5 MILS
Source Bonding Pad Area	5.9 x 13.8 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



BACKSIDE DRAIN R0

GROSS DIE PER 5 INCH WAFER
33,500

PRINCIPAL DEVICE TYPES
2N7002

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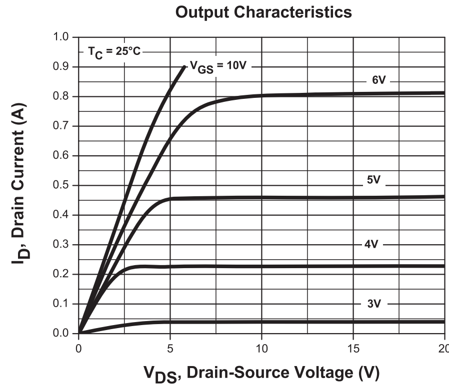
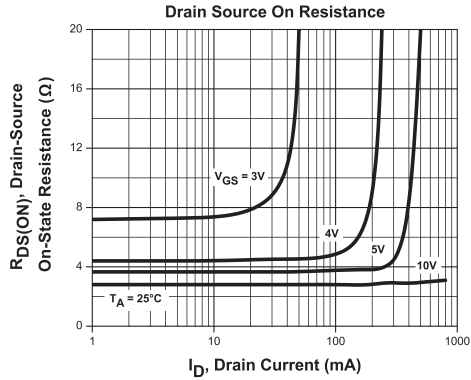
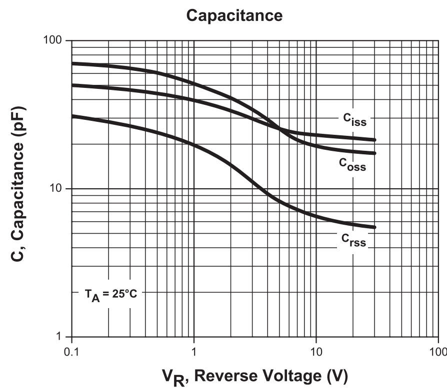
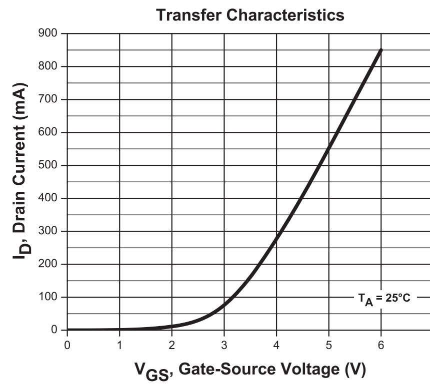
PROCESS CP324

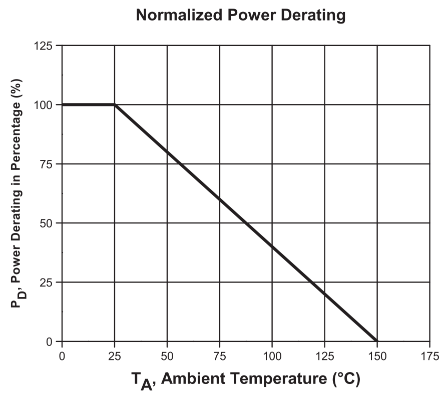
Typical Electrical Characteristics











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